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Understanding <u>Embedded - FPGAs (Field Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

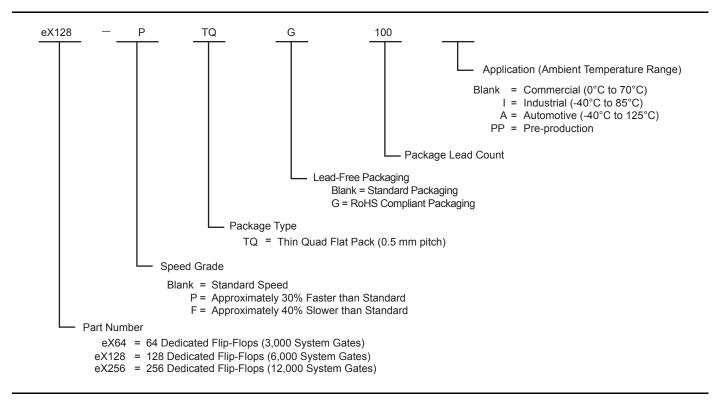
Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	128
Total RAM Bits	-
Number of I/O	41
Number of Gates	3000
Voltage - Supply	2.3V ~ 2.7V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	64-LQFP
Supplier Device Package	64-TQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/ex64-ftq64

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



Ordering Information



eX Device Status

eX Devices	Status
eX64	Production
eX128	Production
eX256	Production

Plastic Device Resources

	User I/Os (Including Clock Buffers)		
Device	TQ64	TQ100	
eX64	41	56	
eX128	46	70	
eX256	_	81	

Note: TQ = Thin Quad Flat Pack

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Module Organization

C-cell and R-cell logic modules are arranged into horizontal banks called Clusters, each of which contains two C-cells and one R-cell in a C-R-C configuration.

Clusters are further organized into modules called SuperClusters for improved design efficiency and device performance, as shown in Figure 1-3. Each SuperCluster is a two-wide grouping of Clusters.

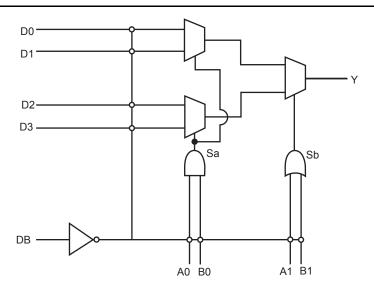


Figure 1-2 • C-Cell

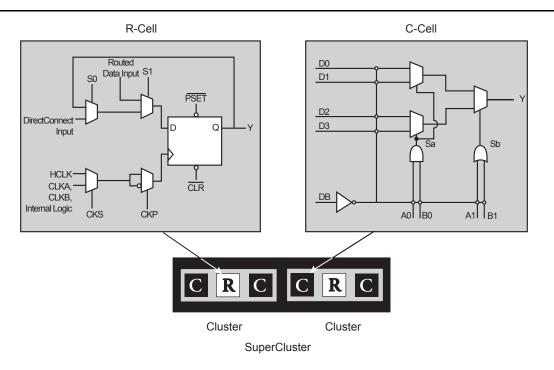


Figure 1-3 • Cluster Organization

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Other Architectural Features

Performance

The combination of architectural features described above enables eX devices to operate with internal clock frequencies exceeding 350 MHz for very fast execution of complex logic functions. The eX family is an optimal platform upon which the functionality previously contained in CPLDs can be integrated. eX devices meet the performance goals of gate arrays, and at the same time, present significant improvements in cost and time to market. Using timing-driven place-and-route tools, designers can achieve highly deterministic device performance.

User Security

Microsemi FuseLock advantage provides the highest level of protection in the FPGA industry against unauthorized modifications. In addition to the inherent strengths of the architecture, special security fuses that are intended to prevent internal probing and overwriting are hidden throughout the fabric of the device. They are located such that they cannot be accessed or bypassed without destroying the rest of the device, making Microsemi antifuse FPGAs highly resistant to both invasive and more subtle noninvasive attacks.

Look for this symbol to ensure your valuable IP is secure. The FuseLock Symbol on the FPGA ensures that the device is safeguarded to cryptographic attacks.



Figure 1-7 • Fuselock

For more information, refer to Implementation of Security in Microsemi Antifuse FPGAs application note.

I/O Modules

Each I/O on an eX device can be configured as an input, an output, a tristate output, or a bidirectional pin. Even without the inclusion of dedicated I/O registers, these I/Os, in combination with array registers, can achieve clock-to-out (pad-to-pad) timing as fast as 3.9 ns. I/O cells in eX devices do not contain embedded latches or flip-flops and can be inferred directly from HDL code. The device can easily interface with any other device in the system, which in turn enables parallel design of system components and reduces overall design time.

All unused I/Os are configured as tristate outputs by Microsemi's Designer software, for maximum flexibility when designing new boards or migrating existing designs. Each I/O module has an available pull-up or pull-down resistor of approximately 50 k Ω that can configure the I/O in a known state during power-up. Just shortly before V_{CCA} reaches 2.5 V, the resistors are disabled and the I/Os will be controlled by user logic.

Table 1-2 describes the I/O features of eX devices. For more information on I/Os, refer to *Microsemi eX, SX-A, and RT54SX-S I/Os* application note.

Table 1-2 • I/O Features

Function	Description		
Input Buffer Threshold	• 5.0V TTL		
Selection	3.3V LVTTL		
	2.5V LVCMOS2		
Nominal Output Drive	5.0V TTL/CMOS		
	3.3V LVTTL		
	• 2.5V LVCMOS 2		
Output Buffer	"Hot-Swap" Capability		
	I/O on an unpowered device does not sink current		
	Can be used for "cold sparing"		
	Selectable on an individual I/O basis		
	Individually selectable low-slew option		
Power-Up	Individually selectable pull ups and pull downs during power-up (default is to power up in tristate)		
	Enables deterministic power-up of device		
	V _{CCA} and V _{CCI} can be powered in any order		

The eX family supports mixed-voltage operation and is designed to tolerate 5.0 V inputs in each case. A detailed description of the I/O pins in eX devices can be found in "Pin Description" on page 1-31.

Hot-Swapping

eX I/Os are configured to be hot-swappable. During power-up/down (or partial up/down), all I/Os are tristated, provided V_{CCA} ramps up within a diode drop of V_{CCI} . V_{CCA} and V_{CCI} do not have to be stable. during power-up/down, and they do not require a specific power-up or power-down sequence in order to avoid damage to the eX devices. In addition, all outputs can be programmed to have a weak resistor pull-up or pull-down for output tristate at power-up. After the eX device is plugged into an electrically active system, the device will not degrade the reliability of or cause damage to the host system. The device's output pins are driven to a high impedance state until normal chip operating conditions are reached. Please see the application note, *Microsemi SX-A and RT54SX-S Devices in Hot-Swap and Cold-Sparing Applications*, which also applies to the eX devices, for more information on hot swapping.

Power Requirements

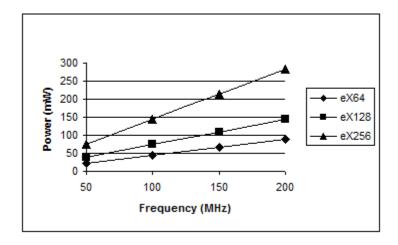
Power consumption is extremely low for the eX family due to the low capacitance of the antifuse interconnects. The antifuse architecture does not require active circuitry to hold a charge (as do SRAM or EPROM), making it the lowest-power FPGA architecture available today.

Low Power Mode

The eX family has been designed with a Low Power Mode. This feature, activated with setting the special LP pin to HIGH for a period longer than 800 ns, is particularly useful for battery-operated systems where battery life is a primary concern. In this mode, the core of the device is turned off and the device consumes minimal power with low standby current. In addition, all input buffers are turned off, and all outputs and bidirectional buffers are tristated when the device enters this mode. Since the core of the device is turned off, the states of the registers are lost. The device must be re-initialized when returning to normal operating mode. I/Os can be driven during LP mode. For details, refer to the *Design for Low Power in Microsemi Antifuse FPGAs* application note under the section Using the LP Mode Pin on eX Devices. Clock pins should be driven either HIGH or LOW and should not float; otherwise, they will draw current and burn power. The device must be re-initialized when exiting LP mode.

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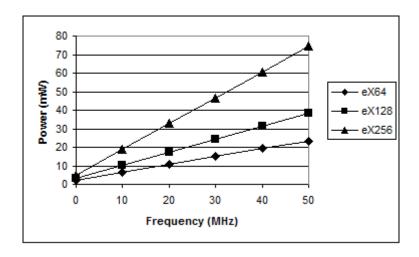
Figure 1-8 to Figure 1-11 on page 1-9 show some sample power characteristics of eX devices.



Notes:

- 1. Device filled with 16-bit counters.
- 2. VCCA, VCCI = 2.7 V, device tested at room temperature.

Figure 1-8 • eX Dynamic Power Consumption – High Frequency



Notes:

- 1. Device filled with 16-bit counters.
- 2. VCCA, VCCI = 2.7 V, device tested at room temperature.

Figure 1-9 • eX Dynamic Power Consumption – Low Frequency

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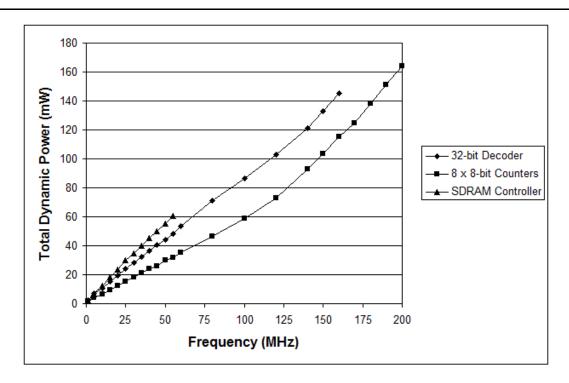


Figure 1-10 • Total Dynamic Power (mW)

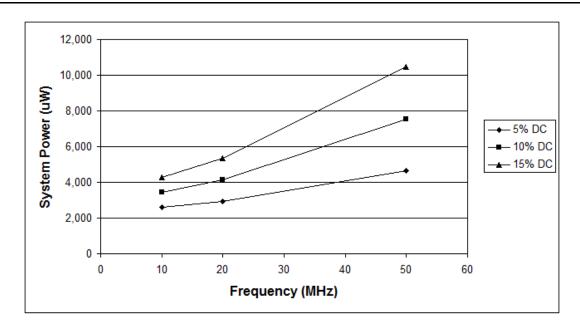


Figure 1-11 • System Power at 5%, 10%, and 15% Duty Cycle

Boundary Scan Testing (BST)

All eX devices are IEEE 1149.1 compliant. eX devices offer superior diagnostic and testing capabilities by providing Boundary Scan Testing (BST) and probing capabilities. These functions are controlled through the special test pins (TMS, TDI, TCK, TDO and TRST). The functionality of each pin is defined by two available modes: Dedicated and Flexible, and is described in Table 1-4. In the dedicated test mode, TCK, TDI, and TDO are dedicated pins and cannot be used as regular I/Os. In flexible mode (default mode), TMS should be set HIGH through a pull-up resistor of 10 k Ω . TMS can be pulled LOW to initiate the test sequence.

Table 1-4 • Boundary Scan Pin Functionality

Dedicated Test Mode	Flexible Mode		
TCK, TDI, TDO are dedicated BST pins	TCK, TDI, TDO are flexible and may be used as I/Os		
No need for pull-up resistor for TMS and TDI	Use a pull-up resistor of 10 k Ω on TMS		

Dedicated Test Mode

In Dedicated mode, all JTAG pins are reserved for BST; designers cannot use them as regular I/Os. An internal pull-up resistor is automatically enabled on both TMS and TDI pins, and the TMS pin will function as defined in the IEEE 1149.1 (JTAG) specification.

To select Dedicated mode, users need to reserve the JTAG pins in Microsemi's Designer software by checking the **Reserve JTAG** box in the Device Selection Wizard (Figure 1-12). JTAG pins comply with LVTTL/TTL I/O specification regardless of whether they are used as a user I/O or a JTAG I/O. Refer to the "3.3 V LVTTL Electrical Specifications" section and "5.0 V TTL Electrical Specifications" section on page 1-18 for detailed specifications.



Figure 1-12 • Device Selection Wizard

Flexible Mode

In Flexible Mode, TDI, TCK and TDO may be used as either user I/Os or as JTAG input pins. The internal resistors on the TMS and TDI pins are disabled in flexible JTAG mode, and an external 10 k Ω pull-resistor to V_{CCI} is required on the TMS pin.

To select the Flexible mode, users need to clear the check box for **Reserve JTAG** in the Device Selection Wizard in Microsemi's Designer software. The functionality of TDI, TCK, and TDO pins is controlled by the BST TAP controller. The TAP controller receives two control inputs, TMS and TCK. Upon power-up, the TAP controller enters the Test-Logic-Reset state. In this state, TDI, TCK, and TDO function as user I/Os. The TDI, TCK, and TDO pins are transformed from user I/Os into BST pins when the TMS pin is LOW at the first rising edge of TCK. The TDI, TCK, and TDO pins return to user I/Os when TMS is held HIGH for at least five TCK cycles.

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Table 1-5 describes the different configuration requirements of BST pins and their functionality in different modes.

Table 1-5 • Boundary-Scan Pin Configurations and Functions

Mode	Designer "Reserve JTAG" Selection	TAP Controller State
Dedicated (JTAG)	Checked	Any
Flexible (User I/O)	Unchecked	Test-Logic-Reset
Flexible (JTAG)	Unchecked	Any EXCEPT Test-Logic-Reset

TRST Pin

The TRST pin functions as a dedicated Boundary-Scan Reset pin when the **Reserve JTAG Test Reset** option is selected, as shown in Figure 1-12. An internal pull-up resistor is permanently enabled on the TRST pin in this mode. It is recommended to connect this pin to GND in normal operation to keep the JTAG state controller in the Test-Logic-Reset state. When JTAG is being used, it can be left floating or be driven HIGH.

When the **Reserve JTAG Test Reset** option is not selected, this pin will function as a regular I/O. If unused as an I/O in the design, it will be configured as a tristated output.

JTAG Instructions

Table 1-6 lists the supported instructions with the corresponding IR codes for eX devices.

Table 1-6 • JTAG Instruction Code

Instructions (IR4: IR0)	Binary Code
EXTEST	00000
SAMPLE / PRELOAD	00001
INTEST	00010
USERCODE	00011
IDCODE	00100
HIGHZ	01110
CLAMP	01111
Diagnostic	10000
BYPASS	11111
Reserved	All others

Table 1-7 lists the codes returned after executing the IDCODE instruction for eX devices. Note that bit 0 is always "1." Bits 11-1 are always "02F", which is Microsemi SoC Products Group's manufacturer code.

Table 1-7 • IDCODE for eX Devices

Device	Revision	Bits 31-28	Bits 27-12
eX64	0	8	40B2, 42B2
eX128	0	9	40B0, 42B0
eX256	0	9	40B5, 42B5
eX64	1	А	40B2, 42B2
eX128	1	В	40B0, 42B0
eX256	1	В	40B5, 42B5



Design Considerations

The TDI, TCK, TDO, PRA, and PRB pins should not be used as input or bidirectional ports. Since these pins are active during probing, critical signals input through these pins are not available while probing. In addition, the Security Fuse should not be programmed because doing so disables the probe circuitry. It is recommended to use a series 70Ω termination resistor on every probe connector (TDI, TCK, TMS, TDO, PRA, PRB). The 70Ω series termination is used to prevent data transmission corruption during probing and reading back the checksum.

Table 1-8 • Device Configuration Options for Probe Capability (TRST pin reserved)

JTAG Mode	TRST ¹	Security Fuse Programmed	PRA, PRB ²	TDI, TCK, TDO ²
Dedicated	LOW	No	User I/O ³	Probing Unavailable
Flexible	LOW	No	User I/O ³	User I/O ³
Dedicated	HIGH	No	Probe Circuit Outputs	Probe Circuit Inputs
Flexible	HIGH	No	Probe Circuit Outputs	Probe Circuit Inputs
_	-	Yes	Probe Circuit Secured	Probe Circuit Secured

Notes:

- 1. If TRST pin is not reserved, the device behaves according to TRST = HIGH in the table.
- 2. Avoid using the TDI, TCK, TDO, PRA, and PRB pins as input or bidirectional ports. Since these pins are active during probing, input signals will not pass through these pins and may cause contention.
- 3. If no user signal is assigned to these pins, they will behave as unused I/Os in this mode. Unused pins are automatically tristated by Microsemi Designer software.

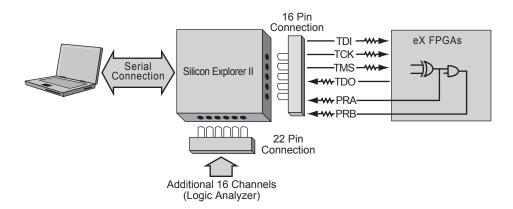


Figure 1-13 • Silicon Explorer II Probe Setup

Development Tool Support

The eX family of FPGAs is fully supported by both Libero® Integrated Design Environment and Designer FPGA Development software. Libero IDE is a design management environment that streamlines the design flow. Libero IDE provides an integrated design manager that seamlessly integrates design tools while guiding the user through the design flow, managing all design and log files, and passing necessary design data among tools. Additionally, Libero IDE allows users to integrate both schematic and HDL synthesis into a single flow and verify the entire design in a single environment. Libero IDE includes Synplify® for Microsemi from Synplicity®, ViewDraw for Microsemi from Mentor Graphics, ModelSim® HDL Simulator from Mentor Graphics®, WaveFormer Lite™ from SynaptiCAD™, and Designer software from Microsemi. Refer to the *Libero IDE flow* (located on Microsemi SoC Product Group's website) diagram for more information.



Power Dissipation

Power consumption for eX devices can be divided into two components: static and dynamic.

Static Power Component

The power due to standby current is typically a small component of the overall power. Typical standby current for eX devices is listed in the Table 1-11 on page 1-16. For example, the typical static power for eX128 at 3.3 V V_{CCl} is:

ICC * VCCA = $795 \mu A \times 2.5 V = 1.99 mW$

Dynamic Power Component

Power dissipation in CMOS devices is usually dominated by the dynamic power dissipation. This component is frequency-dependent and a function of the logic and the external I/O. Dynamic power dissipation results from charging internal chip capacitance due to PC board traces and load device inputs. An additional component of the dynamic power dissipation is the totem pole current in the CMOS transistor pairs. The net effect can be associated with an equivalent capacitance that can be combined with frequency and voltage to represent dynamic power dissipation.

Dynamic power dissipation = $CEQ * VCCA^2 x F$

where:

CEQ = Equivalent capacitance

F = switching frequency

Equivalent capacitance is calculated by measuring ICCA at a specified frequency and voltage for each circuit component of interest. Measurements have been made over a range of frequencies at a fixed value of VCC. Equivalent capacitance is frequency-independent, so the results can be used over a wide range of operating conditions. Equivalent capacitance values are shown below.

CEQ Values for eX Devices

Combinatorial modules (Ceqcm) 1.70 pF
Sequential modules (Ceqsm) 1.70 pF
Input buffers (Ceqi) 1.30 pF
Output buffers (Ceqo) 7.40 pF
Routed array clocks (Ceqcr) 1.05 pF

The variable and fixed capacitance of other device components must also be taken into account when estimating the dynamic power dissipation.

Table 1-12 shows the capacitance of the clock components of eX devices.

Table 1-12 • Capacitance of Clock Components of eX Devices

	eX64	eX128	eX256
Dedicated array clock – variable (Ceqhv)	0.85 pF	0.85 pF	0.85 pF
Dedicated array clock – fixed (Ceqhf)	18.00 pF	20.00 pF	25.00 pF
Routed array clock A (r1)	23.00 pF	28.00 pF	35.00 pF
Routed array clock B (r2)	23.00 pF	28.00 pF	35.00 pF



Thermal Characteristics

The temperature variable in the Designer software refers to the junction temperature, not the ambient temperature. This is an important distinction because the heat generated from dynamic power consumption is usually hotter than the ambient temperature. EQ 1, shown below, can be used to calculate junction temperature.

EQ 1

Junction Temperature = $\Delta T + T_a(1)$

Where:

T_a = Ambient Temperature

 ΔT = Temperature gradient between junction (silicon) and ambient = θ_{ja} * P

P = Power

 θ_{ja} = Junction to ambient of package. θ_{ja} numbers are located in the "Package Thermal Characteristics" section below.

Package Thermal Characteristics

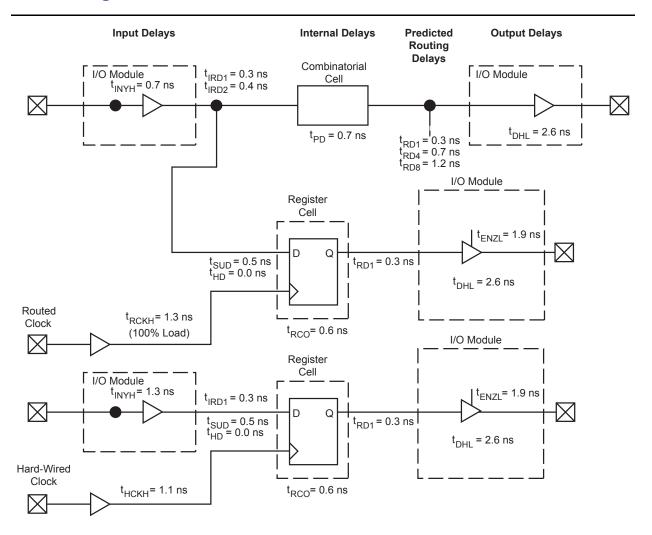
The device junction-to-case thermal characteristic is θ_{jc} , and the junction-to-ambient air characteristic is θ_{ja} . The thermal characteristics for θ_{ja} are shown with two different air flow rates. θ_{jc} is provided for reference. The maximum junction temperature is 150°C.

The maximum power dissipation allowed for eX devices is a function of θ_{ja} . A sample calculation of the absolute maximum power dissipation allowed for a TQFP 100-pin package at commercial temperature and still air is as follows:

$$\text{Maximum Power Allowed} = \frac{\text{Max. junction temp. (°C)} - \text{Max. ambient temp. (°C)}}{\theta_{ja}(°C/W)} = \frac{150°C - 70°C}{33.5°C/W} = 2.39W$$

			$ heta_{\sf ja}$			
Package Type	Pin Count	$ heta_{ extsf{jc}}$	Still Air	1.0 m/s 200 ft/min	2.5 m/s 500 ft/min	Units
Thin Quad Flat Pack (TQFP)	64	12.0	42.4	36.3	34.0	°C/W
Thin Quad Flat Pack (TQFP)	100	14.0	33.5	27.4	25.0	°C/W

eX Timing Model



Note: Values shown for eX128-P, worst-case commercial conditions (5.0 V, 35 pF Pad Load).

Figure 1-14 • eX Timing Model

Hardwired Clock

External Setup =
$$t_{INYH} + t_{IRD1} + t_{SUD} - t_{HCKH}$$

= 0.7 + 0.3 + 0.5 - 1.1 = 0.4 ns
Clock-to-Out (Pad-to-Pad), typical
= $t_{HCKH} + t_{RCO} + t_{RD1} + t_{DHL}$
= 1.1 + 0.6 + 0.3 + 2.6 = 4.6 ns

Routed Clock

External Setup =
$$t_{INYH} + t_{IRD2} + t_{SUD} - t_{RCKH}$$

= 0.7 + 0.4 + 0.5 - 1.3= 0.3 ns
Clock-to-Out (Pad-to-Pad), typical
= $t_{RCKH} + t_{RCO} + t_{RD1} + t_{DHL}$
= 1.3+ 0.6 + 0.3 + 2.6 = 4.8 ns

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Timing Characteristics

Timing characteristics for eX devices fall into three categories: family-dependent, device-dependent, and design-dependent. The input and output buffer characteristics are common to all eX family members. Internal routing delays are device-dependent. Design dependency means actual delays are not determined until after placement and routing of the user's design are complete. Delay values may then be determined by using the Timer utility or performing simulation with post-layout delays.

Critical Nets and Typical Nets

Propagation delays are expressed only for typical nets, which are used for initial design performance evaluation. Critical net delays can then be applied to the most timing critical paths. Critical nets are determined by net property assignment prior to placement and routing. Up to six percent of the nets in a design may be designated as critical.

Long Tracks

Some nets in the design use long tracks. Long tracks are special routing resources that span multiple rows, columns, or modules. Long tracks employ three to five antifuse connections. This increases capacitance and resistance, resulting in longer net delays for macros connected to long tracks. Typically, no more than six percent of nets in a fully utilized device require long tracks. Long tracks contribute approximately 4 ns to 8.4 ns delay. This additional delay is represented statistically in higher fanout routing delays.

Timing Derating

eX devices are manufactured with a CMOS process. Therefore, device performance varies according to temperature, voltage, and process changes. Minimum timing parameters reflect maximum operating voltage, minimum operating temperature, and best-case processing. Maximum timing parameters reflect minimum operating voltage, maximum operating temperature, and worst-case processing.

Temperature and Voltage Derating Factors

Table 1-16 • Temperature and Voltage Derating Factors
(Normalized to Worst-Case Commercial, T., = 70°C, VCCA = 2.3V)

	Junction Temperature (T _J)						
VCCA	-55	-40	0	25	70	85	125
2.3	0.79	0.80	0.87	0.88	1.00	1.04	1.13
2.5	0.74	0.74	0.81	0.83	0.93	0.97	1.06
2.7	0.69	0.70	0.76	0.78	0.88	0.91	1.00

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Table 1-18 • eX Family Timing Characteristics (Worst-Case Commercial Conditions VCCA = 2.3 V, VCCI = 4.75 V, $T_J = 70^{\circ}$ C)

		−P S	peed	Std S	speed -F Speed		peed	
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
Dedicated (Hard-Wired) Array Clock Networks								
t _{HCKH}	Input LOW to HIGH (Pad to R-Cell Input)		1.1		1.6		2.3	ns
t _{HCKL}	Input HIGH to LOW (Pad to R-Cell Input)		1.1		1.6		2.3	ns
t _{HPWH}	Minimum Pulse Width HIGH	1.4		2.0		2.8		ns
t _{HPWL}	Minimum Pulse Width LOW	1.4		2.0		2.8		ns
t _{HCKSW}	Maximum Skew		<0.1		<0.1		<0.1	ns
t _{HP}	Minimum Period	2.8		4.0		5.6		ns
f_{HMAX}	Maximum Frequency		357		250		178	MHz
Routed Arra	y Clock Networks							
t _{RCKH}	Input LOW to HIGH (Light Load) (Pad to R-Cell Input) MAX.		1.1		1.6		2.2	ns
t _{RCKL}	Input HIGH to LOW (Light Load) (Pad to R-Cell Input) MAX.		1.0		1.4		2.0	ns
t _{RCKH}	Input LOW to HIGH (50% Load) (Pad to R-Cell Input) MAX.		1.2		1.7		2.4	ns
t _{RCKL}	Input HIGH to LOW (50% Load) (Pad to R-Cell Input) MAX.		1.2		1.7		2.4	ns
t _{RCKH}	Input LOW to HIGH (100% Load) (Pad to R-Cell Input) MAX.		1.3		1.9		2.6	ns
t _{RCKL}	Input HIGH to LOW (100% Load) (Pad to R-Cell Input) MAX.		1.3		1.9		2.6	ns
t _{RPWH}	Min. Pulse Width HIGH	1.5		2.1		3.0		ns
t _{RPWL}	Min. Pulse Width LOW	1.5		2.1		3.0		ns
t _{RCKSW} *	Maximum Skew (Light Load)		0.2		0.3		0.4	ns
t _{RCKSW} *	Maximum Skew (50% Load)		0.1		0.2		0.3	ns
t _{RCKSW} *	Maximum Skew (100% Load)		0.1		0.1		0.2	ns

Note: *Clock skew improves as the clock network becomes more heavily loaded.

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Pin Description

CLKA/B Routed Clock A and B

These pins are clock inputs for clock distribution networks. Input levels are compatible with standard TTL or LVTTL specifications. The clock input is buffered prior to clocking the R-cells. If not used, this pin must be set LOW or HIGH on the board. It must not be left floating.

GND Ground

LOW supply voltage.

HCLK Dedicated (Hardwired) Array Clock

This pin is the clock input for sequential modules. Input levels are compatible with standard TTL or LVTTL specifications. This input is directly wired to each R-cell and offers clock speeds independent of the number of R-cells being driven. If not used, this pin must be set LOW or HIGH on the board. It must not be left floating.

I/O Input/Output

The I/O pin functions as an input, output, tristate, or bidirectional buffer. Based on certain configurations, input and output levels are compatible with standard TTL or LVTTL specifications. Unused I/O pins are automatically tristated by the Designer software.

LP Low Power Pin

Controls the low power mode of the eX devices. The device is placed in the low power mode by connecting the LP pin to logic HIGH. In low power mode, all I/Os are tristated, all input buffers are turned OFF, and the core of the device is turned OFF. To exit the low power mode, the LP pin must be set LOW. The device enters the low power mode 800 ns after the LP pin is driven to a logic HIGH. It will resume normal operation 200 μ s after the LP pin is driven to a logic LOW. LP pin should not be left floating. Under normal operating condition it should be tied to GND via 10 k Ω resistor.

NC No Connection

This pin is not connected to circuitry within the device. These pins can be driven to any voltage or can be left floating with no effect on the operation of the device.

PRA/PRB, I/O Probe A/B

The Probe pin is used to output data from any user-defined design node within the device. This diagnostic pin can be used independently or in conjunction with the other probe pin to allow real-time diagnostic output of any signal path within the device. The Probe pin can be used as a user-defined I/O when verification has been completed. The pin's probe capabilities can be permanently disabled to protect programmed design confidentiality.

TCK, I/O Test Clock

Test clock input for diagnostic probe and device programming. In flexible mode, TCK becomes active when the TMS pin is set LOW (refer to Table 1-4 on page 1-10). This pin functions as an I/O when the boundary scan state machine reaches the "logic reset" state.

TDI, I/O Test Data Input

Serial input for boundary scan testing and diagnostic probe. In flexible mode, TDI is active when the TMS pin is set LOW (refer to Table 1-4 on page 1-10). This pin functions as an I/O when the boundary scan state machine reaches the "logic reset" state.

TDO, I/O Test Data Output

Serial output for boundary scan testing. In flexible mode, TDO is active when the TMS pin is set LOW (refer to Table 1-4 on page 1-10). This pin functions as an I/O when the boundary scan state machine reaches the "logic reset" state. When Silicon Explorer is being used, TDO will act as an output when the "checksum" command is run. It will return to user I/O when "checksum" is complete.



TQ100						
Pin Number	eX64 Function	eX128 Function	eX256 Function			
71	I/O	I/O	I/O			
72	NC	I/O	I/O			
73	NC	NC	I/O			
74	NC	NC	I/O			
75	NC	NC	I/O			
76	NC	I/O	I/O			
77	I/O	I/O	I/O			
78	I/O	I/O	I/O			
79	I/O	I/O	I/O			
80	I/O	I/O	I/O			
81	I/O	I/O	I/O			
82	VCCI	VCCI	VCCI			
83	I/O	I/O	I/O			
84	I/O	I/O	I/O			
85	I/O	I/O	I/O			
86	I/O	I/O	I/O			
87	CLKA	CLKA	CLKA			
88	CLKB	CLKB	CLKB			
89	NC	NC	NC			
90	VCCA	VCCA	VCCA			
91	GND	GND	GND			
92	PRA, I/O	PRA, I/O	PRA, I/O			
93	I/O	I/O	I/O			
94	I/O	I/O	I/O			
95	I/O	I/O	I/O			
96	I/O	I/O	I/O			
97	I/O	I/O	I/O			
98	I/O	I/O	I/O			
99	I/O	I/O	I/O			
100	TCK, I/O	TCK, I/O	TCK, I/O			

Note: *Please read the LP pin descriptions for restrictions on their use.



Datasheet Information

Revision	Changes	Page	
v4.0 (continued)	The "Flexible Mode" section was updated.	1-10	
	Table 1-5 •Boundary-Scan Pin Configurations and Functions is new.	1-11	
	The "TRST Pin" section was updated.		
	The "Probing Capabilities" section is new.	1-12	
	The "Programming" section was updated.	1-12	
	The "Probing Capabilities" section was updated.	1-12	
	The "Silicon Explorer II Probe" section was updated.	1-12	
	The "Design Considerations" section was updated.	1-13	
	The "Development Tool Support" section was updated.	1-13	
	The "Absolute Maximum Ratings*" section was updated.	1-16	
	The "Temperature and Voltage Derating Factors" section was updated.	1-26	
	The "TDI, I/O Test Data Input" section was updated.	1-31	
	The "TDO, I/O Test Data Output" section was updated.		
	The "TMS Test Mode Select" section was updated.	1-32	
	The "TRST, I/O Boundary Scan Reset Pin" section was updated.	1-32	
	All VSV pins were changed to VCCA. The change affected the following pins:		
	64-Pin TQFP – Pin 36		
	100-Pin TQFP – Pin 57		
	49-Pin CSP – Pin D5		
	128-Pin CSP— Pin H11 and Pin J1 for eX256		
	180-Pin CSP – Pins J12 and K2	4.40	
v3.0	The "Recommended Operating Conditions" section has been changed.	1-16	
	The "3.3 V LVTTL Electrical Specifications" section has been updated.	1-18 1-18	
	The "5.0 V TTL Electrical Specifications" section has been updated.		
	The "Total Dynamic Power (mW)" section is new.		
	The "System Power at 5%, 10%, and 15% Duty Cycle" section is new.		
	The "eX Timing Model" section has been updated.	1-22	
v2.0.1	The I/O Features table, Table 1-2 on page 1-6, was updated.	1-6	
	The table, "Standby Power of eX Devices in LP Mode Typical Conditions, VCCA, VCCI = 2.5 V, TJ = 25° C" section, was updated.	1-7	
	"Typical eX Standby Current at 25°C" section is a new table.	1-16	
	The table in the section, "Package Thermal Characteristics" section has been updated for the 49-Pin CSP.	1-21	
	The "eX Timing Model" section has been updated.	1-22	
	The timing numbers found in, "eX Family Timing Characteristics" section have been updated.	1-27	
	The V _{SV} pin has been added to the "Pin Description" section.	1-31	
	Please see the following pin tables for the V_{SV} pin and an important footnote including the pin: "TQ64", "TQ100", "128-Pin CSP", and "180-Pin CSP".	2-1, 2-3, 2-6, 2-11	
	The figure, "TQ64" section has been updated.	2-1	

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Revision	Changes	Page
Advance v0.4	In the Product Profile, the Maximum User I/Os for eX64 was changed to 84.	
	In the Product Profile table, the Maximum User I/Os for eX128 was changed to 100.	1-I
Advance v0.3	The Mechanical Drawings section has been removed from the data sheet. The mechanical drawings are now contained in a separate document, "Package Characteristics and Mechanical Drawings," available on the Actel web site.	
	A new section describing "Clock Resources"has been added.	1-3
	A new table describing "I/O Features"has been added.	1-6
	The "Pin Description"section has been updated and clarified.	1-31
	The original Electrical Specifications table was separated into two tables (2.5V and 3.3/5.0V). In both tables, several different currents are specified for V_{OH} and V_{OL} .	Page 8 and 9
	A new table listing 2.5V low power specifications and associated power graphs were added.	page 9
	Pin functions for eX256 TQ100 have been added to the "TQ100"table.	2-3
	A CS49 pin drawing and pin assignment table including eX64 and eX128 pin functions have been added.	page 26
	A CS128 pin drawing and pin assignment table including eX64, eX128, and eX256 pin functions have been added.	pages 26-27
	A CS180 pin drawing and pin assignment table for eX256 pin functions have been added.	pages 27, 31
Advance v0.2	The following table note was added to the eX Timing Characteristics table for clarification: Clock skew improves as the clock network becomes more heavily loaded.	pages 14-15



Datasheet Categories

Categories

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device, as highlighted in the "eX Device Status" table on page II, is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

Product Brief

The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

Advance

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

Preliminary

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

Production

This version contains information that is considered to be final.

Export Administration Regulations (EAR)

The product described in this datasheet is subject to the Export Administration Regulations (EAR). They could require an approved export license prior to export from the United States. An export includes release of product or disclosure of technology to a foreign national inside or outside the United States.

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